

Product data sheet

### 1. General description

PNP low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

NPN complement: PBSS4130QA.

### 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- High energy efficiency due to less heat generation
- Reduced Printed-Circuit Board (PCB) area requirements
- Solderable side pads
- AEC-Q101 qualified

### 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-30	V
I <sub>C</sub>	collector current		-	-	-1	А
I <sub>CM</sub>	peak collector current	$t_p \le 1 \text{ ms}; \text{ pulsed}$	-	-	-1.5	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	160	240	mΩ

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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		С
2	E	emitter		в
3	С	collector	4 3	۲۳ م ۲
4	С	collector		sym132
			Transparent top view DFN1010D-3 (SOT1215)	

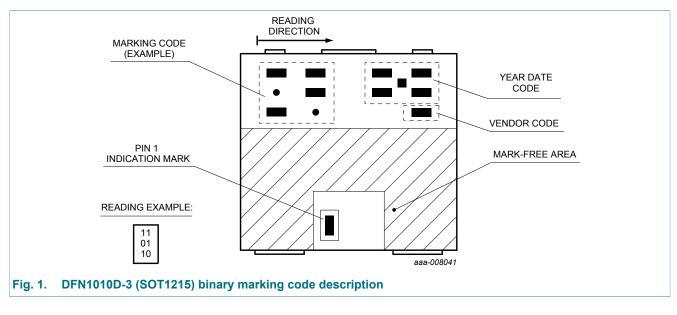
### 6. Ordering information

Table 3.         Ordering information						
Type number	Package					
	Name	Description	Version			
PBSS5130QA	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals	SOT1215			

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBSS5130QA	00 10 10



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### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-30	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-30	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-7	V
I <sub>C</sub>	collector current			-	-1	А
I <sub>CM</sub>	peak collector current	$t_p \le 1 ms$ ; pulsed		-	-1.5	А
I <sub>B</sub>	base current			-	-0.3	А
I <sub>BM</sub>	peak base current	$t_p \le 1 \text{ ms}; \text{ pulsed}$		-	-1	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[3]	-	740	mW
			[4]	-	540	mW
			[5]	-	1000	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

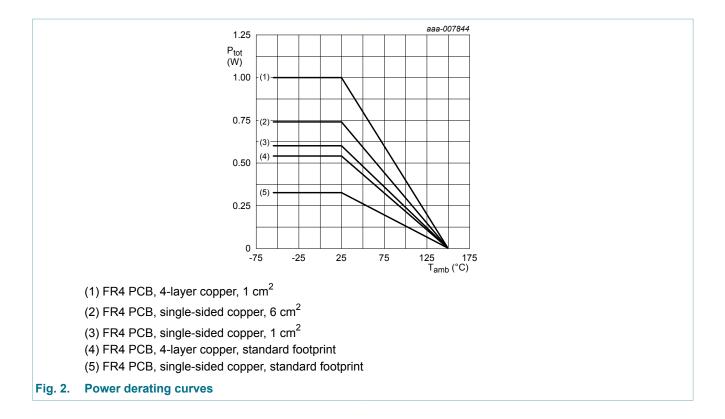
[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

<sup>[5]</sup> Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

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### 9. Thermal characteristics

Table 6. 1	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
uig-a)	thermal resistance	in free air	[1]	-	-	385	K/W
	from junction to		[2]	-	-	209	K/W
	ampient		[3]	-	-	169	K/W
			[4]	-	-	232	K/W
			[5]	-	-	125	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

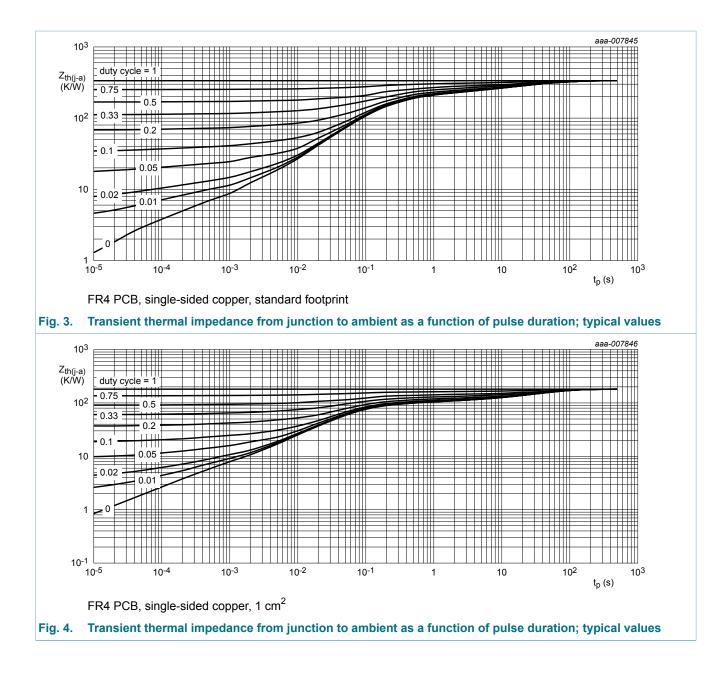
[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

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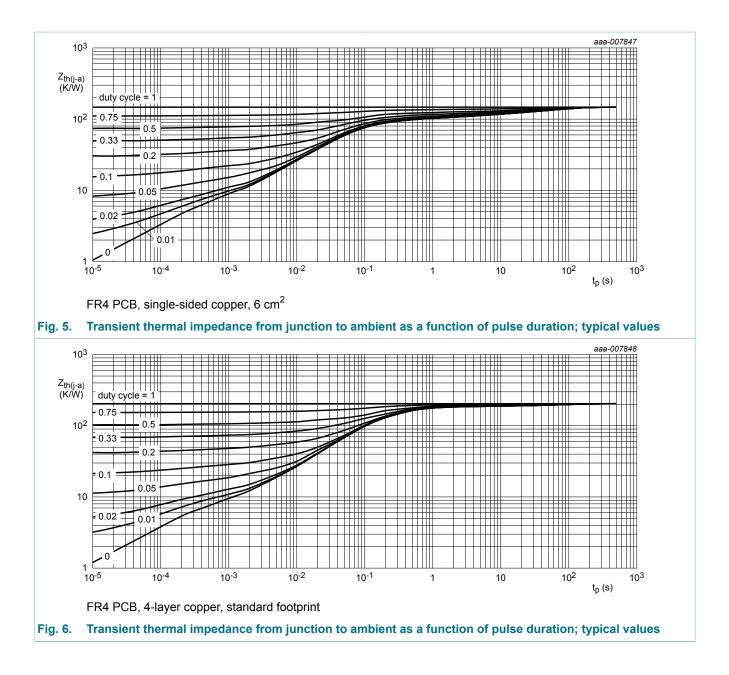


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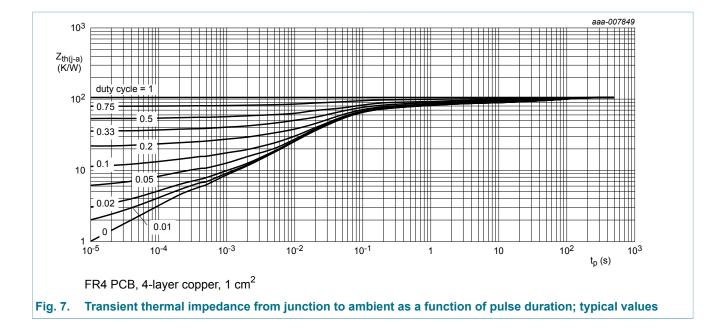


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## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -24 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -24 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -24 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -2 \text{ V; } I_{C} = -100 \text{ mA; } t_{p} \le 300  \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C; pulsed}$	250	425	-	
		$V_{CE} = -2 \text{ V; } I_C = -500 \text{ mA; } t_p \le 300  \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C; pulsed}$	180	295	-	
		$V_{CE} = -2 \text{ V; } I_C = -1 \text{ A; } t_p \le 300  \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C; } \text{pulsed}$	130	200	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = -500 mA; $I_{B}$ = -50 mA; $t_{p}$ ≤ 300 µs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-85	-130	mV
		$I_{C}$ = -1 A; $I_{B}$ = -50 mA; $t_{p}$ ≤ 300 μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-180	-260	mV
		$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-160	-240	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; $\overline{\delta} \le 0.02$ ; $T_{amb}$ = 25 °C	-	160	240	mΩ

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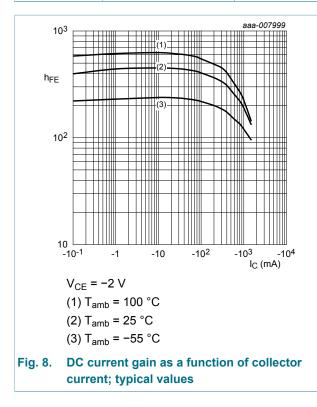
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>BEsat</sub> base-emi voltage		$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-0.88	-1	V
		$I_{C}$ = -1 A; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	-0.93	-1.05	V
		$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	-0.96	-1.1	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$\label{eq:VcE} \begin{array}{l} V_{CE} = \text{-2 V; } I_{C} = \text{-0.5 A; pulsed;} \\ t_{p} \leq 300 \ \mu s; \ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^{\circ}C \end{array}$	-	-0.78	-0.9	V
t <sub>d</sub>	delay time	$V_{CC}$ = -10 V; I <sub>C</sub> = -0.5 A; I <sub>Bon</sub> = -25 mA; I <sub>Boff</sub> = 25 mA; T <sub>amb</sub> = 25 °C	-	10	-	ns
t <sub>r</sub>	rise time		-	30	-	ns
t <sub>on</sub>	turn-on time		-	40	-	ns
t <sub>s</sub>	storage time		-	270	-	ns
t <sub>f</sub>	fall time		-	45	-	ns
t <sub>off</sub>	turn-off time		-	315	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; I <sub>C</sub> = -50 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	120	170	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	14	16	pF



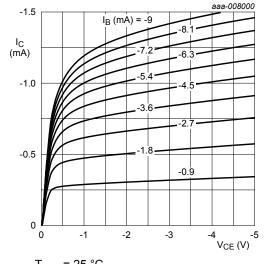
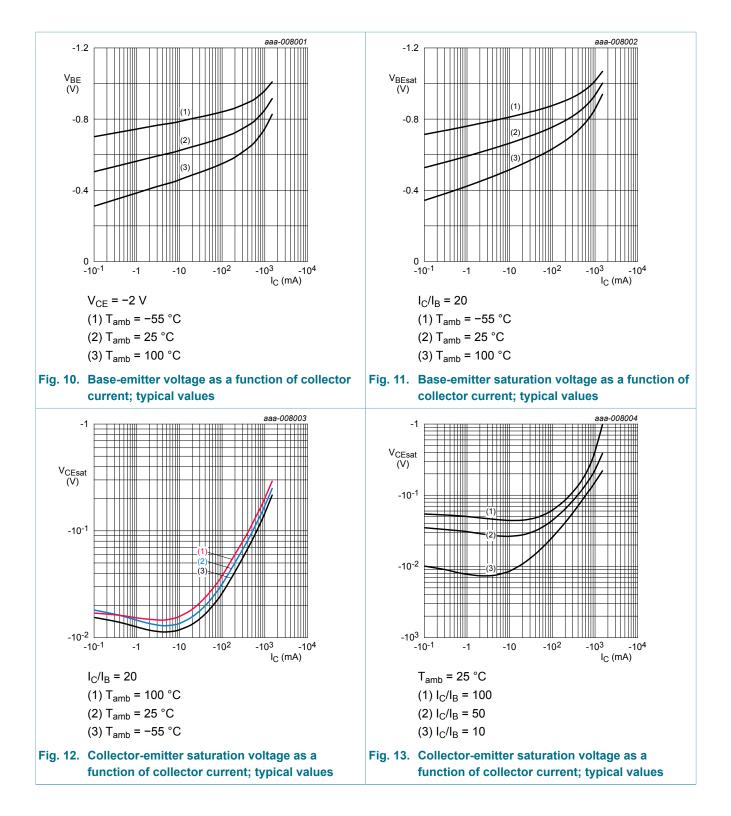




Fig. 9. Collector current as a function of collectoremitter voltage; typical values

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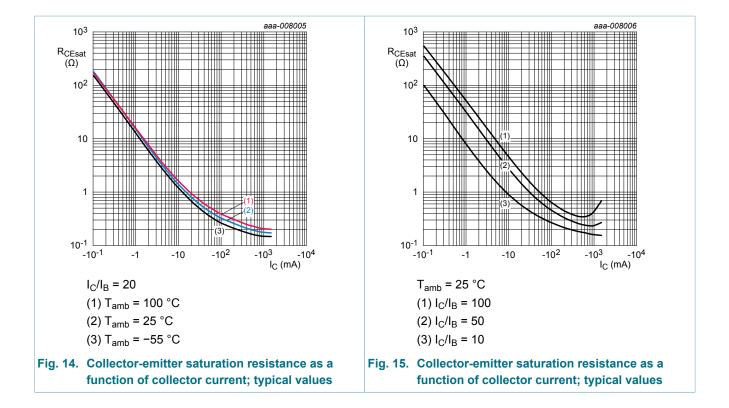
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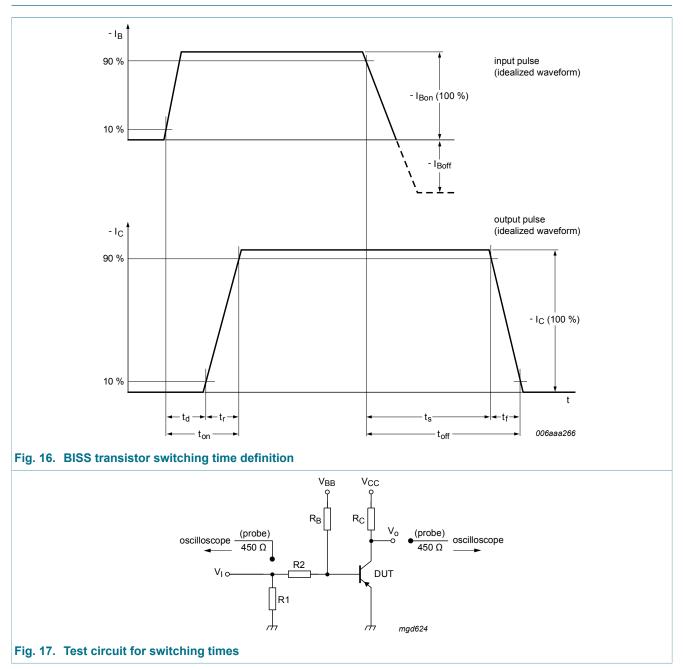
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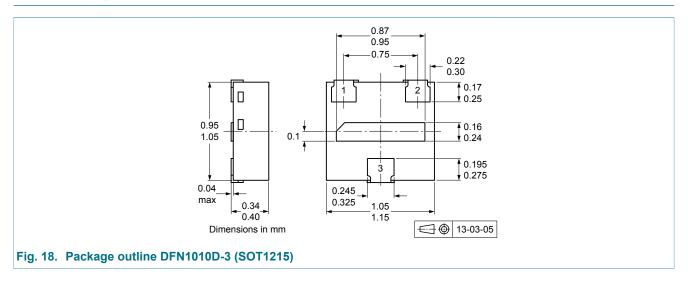
### **11. Test information**



This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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# 12. Package outline

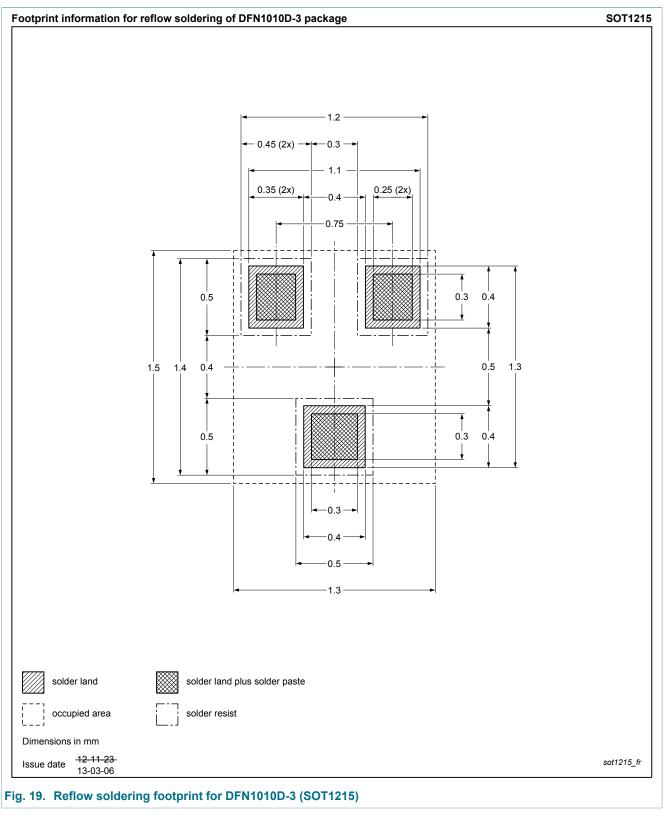


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### 13. Soldering



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# 14. Revision history

Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS5130QA v.1	20130828	Product data sheet	-	-	

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### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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